

What is claimed is:

1 1. A flexible electronic device comprising: a flexible film;
2 a substrate formed on the flexible film, the substrate being
3 different from the material of said flexible film and thickness
4 of said substrate is larger than 0 μm and not larger than 200
5 μm ; and a thin film device formed on the substrate.

1 2. The flexible electronic device according to claim 1,
2 wherein said flexible electronic device is formed by laminating
3 at least two or more components.

1 3. The flexible electronic device according to claim 1,
2 wherein said thin film device is a thin film transistor formed
3 of a silicon thin film.

1 4. The flexible electronic device according to claim 1,
2 wherein said substrate is an insulating substrate.

1 5. The flexible electronic device according to claim 4,
2 wherein said insulating substrate is a glass substrate.

1 6. The flexible electronic device according to claim 1,
2 wherein said flexible film is an insulating film.

1 7. The flexible electronic device according to claim 1,
2 wherein said flexible film has a thermal conductivity higher
3 than 0.01 W/cm-deg.

1 8. The flexible electronic device according to claim 1,
2 wherein said flexible film is a laminated structure at least
3 comprising a film having a thermal conductivity higher than
4 0.01 W/ cm-deg and an insulating film.

1 9. A production method of a flexible electronic device
2 comprising the steps of:
3 forming a thin film device on a substrate;
4 adhering a protection film onto said thin film device;
5 etching said substrate from a back surface thereof such that
6 residual thickness of said substrate is larger than 0 μm and
7 not larger than 200 μm ;
8 adhering a flexible film onto etched surface of said substrate;
9 and peeling said protection film from said thin film device
10 after a step of said adhering said flexible film.

1 10. The production method of a flexible electronic device
2 according to claim 9, wherein said thin film device is a thin
3 film transistor formed of a silicon thin film.

1 11. The production method of a flexible electronic device
2 according to claim 9, wherein said substrate is an insulating
3 substrate.

1 12. The production method of a flexible electronic device
2 according to claim 9, wherein said insulating substrate is a
3 glass substrate.

1 13. The production method of a flexible electronic device
2 according to claim 9, wherein said flexible film is an insulating
3 film.

1 14. The production method of a flexible electronic device
2 according to claim 9, wherein said flexible film has a thermal
3 conductivity higher than 0.01 W/cm·deg.

1 15. The production method of a flexible electronic device
2 according to claim 9, wherein said flexible film is a laminated
3 structure at least comprising a film having a thermal
4 conductivity higher than 0.01 W/cm·deg and an insulating film.

1 16. A production method of a flexible electronic device,
2 comprising the steps of laminating a first glass substrate and
3 a second glass substrate, each having a thin film device formed
4 on one surface thereof, so as for said thin film device formed
5 surfaces to adhere to each other; adhering a protection sheet
6 on the surface of said first glass substrate other than said
7 thin film device formed surface thereof; etching the surface
8 of said second glass substrate other than said thin film device
9 formed surface thereof until the residual thickness of said
10 second glass substrate becomes larger than 0 μm and not larger
11 than 200 μm ; adhering a flexible sheet onto the etched surface
12 of said first glass substrate; peeling said protection sheet;
13 etching the surface of said first glass substrate other than
14 said thin film device formed surface thereof until the residual

15 thickness of said first glass substrate becomes larger than
16 0 μm and not larger than 200 μm ; and adhering a flexible film
17 on to the etched surface of said first glass substrate, wherein
18 these steps are successively performed.

1 17. A production method of a flexible electronic device,
2 comprising the steps of laminating a pair of a first glass
3 substrate and a second glass substrate, each having a thin film
4 device formed on one surface thereof, so as for said thin film
5 device formed surfaces to adhere to each other; etching the
6 surfaces of said first glass substrate and said second glass
7 substrate respectively other than said thin film device formed
8 surfaces thereof until the respective residual thicknesses of
9 said first glass substrate and said second glass substrate become
10 larger than 0 μm and not larger than 200 μm ; and adhering flexible
11 films respectively onto the etched surfaces of said first glass
12 substrate and said second glass substrate, wherein these steps
13 are performed successively.

1 18. The production method of a flexible electronic device
2 according to claim 16, wherein said flexible devices are liquid
3 crystal display devices.

1 19. The production method of a flexible electronic device
2 according to claim 17, wherein said flexible devices are liquid
3 crystal display devices.

1 20. The production method of a flexible electronic device
2 according to claim 16, wherein said flexible films have
3 polarizing function and phase difference function.

1 21. The production method of a flexible electronic device
2 according to claim 17, wherein said flexible films have
3 polarizing function and phase difference function.

1 22. The production method of a flexible electronic device
2 according to any one of claims 9, 16 and 17, wherein in said
3 etching step or in each of said etching steps, a confirmation
4 substep for measuring the weight or thickness of the substrate
5 being etched is performed several times in the course of the
6 etching step.